

6MBI50UA-120



IGBT Module U-Series 1200V / 50A 6 in one-package

■ Features

- High speed switching
- Voltage drive
- Low inductance module structure

■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

| Item | Symbol | Conditions | Rating | Unit | |
|-----------------------------|-------------------------------------|------------------|----------------------|------|-----|
| Collector-Emitter voltage | V _{CEs} | | 1200 | V | |
| Gate-Emitter voltage | V _{GES} | | ±20 | V | |
| Collector current | I _c | Continuous | T _c =25°C | 75 | A |
| | | | T _c =80°C | 50 | |
| | I _{cp} | 1ms | T _c =25°C | 150 | |
| | | | T _c =80°C | 100 | |
| | -I _c | | | 50 | |
| -I _c pulse | | | 100 | | |
| Collector Power Dissipation | P _c | 1 device | 275 | W | |
| Junction temperature | T _j | | +150 | °C | |
| Storage temperature | T _{stg} | | -40 to +125 | | |
| Isolation voltage | between terminal and copper base *1 | V _{iso} | AC:1min. | 2500 | VAC |
| | between thermistor and others *2 | | | | |
| Screw Torque | Mounting *3 | - | 3.5 | N·m | |

*1 : All terminals should be connected together when isolation test will be done.

*2 : Two thermistor terminals should be connected together, each other terminals should be connected together and shorted to base plate when isolation test will be done.

*3 :Recommendable value : 2.5 to 3.5 N·m(M5)

● Electrical characteristics (at T_j=25°C unless otherwise specified)

| Item | Symbols | Conditions | Characteristics | | | Unit | |
|--------------------------------------|------------------------------------|---|-----------------------|------|------|------|---|
| | | | Min. | Typ. | Max. | | |
| Zero gate voltage collector current | I _{CEs} | V _{GE} =0V, V _{CE} =1200V | - | - | 1.0 | mA | |
| Gate-Emitter leakage current | I _{GES} | V _{CE} =0V, V _{GE} =±20V | - | - | 200 | nA | |
| Gate-Emitter threshold voltage | V _{GE(th)} | V _{CE} =20V, I _c =50mA | 4.5 | 6.5 | 8.5 | V | |
| Collector-Emitter saturation voltage | V _{CE(sat)} (terminal) | V _{GE} =15V, I _c =50A | T _j =25°C | - | 2.00 | 2.35 | V |
| | | | T _j =125°C | - | 2.25 | - | |
| | V _{CE(sat)} (chip) | | T _j =25°C | - | 1.75 | 2.10 | |
| | | | T _j =125°C | - | 2.00 | - | |
| Input capacitance | C _{ies} | V _{CE} =10V, V _{GE} =0V, f=1MHz | - | 6 | - | nF | |
| Turn-on time | t _{on} | V _{CC} =600V | - | 0.36 | 1.20 | μs | |
| | t _r | I _c =50A | - | 0.21 | 0.60 | | |
| | t _{r(i)} | V _{GE} =±15V | - | 0.03 | - | | |
| Turn-off time | t _{off} | R _G =22 Ω | - | 0.37 | 1.00 | μs | |
| | t _f | | - | 0.07 | 0.30 | | |
| Forward on voltage | V _F (terminal) | V _{GE} =0V I _F =50A | T _j =25°C | - | 1.85 | 2.15 | V |
| | | | T _j =125°C | - | 1.95 | - | |
| | V _F (chip) | | T _j =25°C | - | 1.60 | 1.90 | |
| | | | T _j =125°C | - | 1.70 | - | |
| Reverse recovery time | t _{rr} | I _F =50A | - | - | 0.35 | μs | |
| Lead resistance, terminal-chip*4 | R _{lead} | | - | 4.1 | - | mΩ | |
| Thermistor | Resistance | T=25°C | - | 5000 | - | Ω | |
| | | T=100°C | 465 | 495 | 520 | | |
| | B value | B | T=25/50°C | 3305 | 3375 | 3450 | K |

*4:Biggest internal terminal resistance among arm.

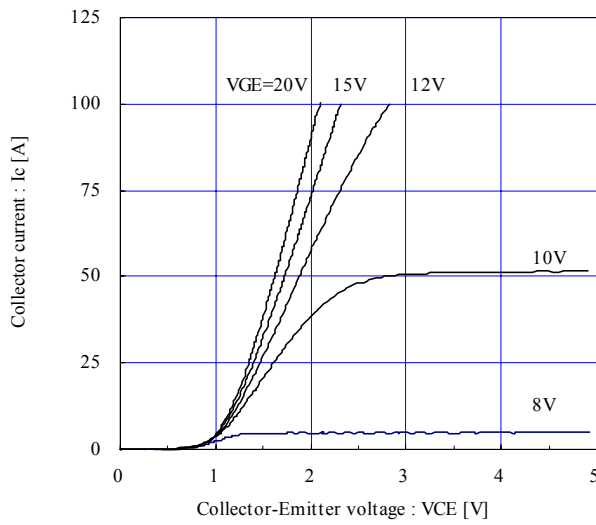
● Thermal resistance characteristics

| Items | Symbols | Conditions | Characteristics | | | Unit |
|----------------------------|-------------------------|-----------------------|-----------------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Thermal resistance | R _{th(j-c)} | IGBT | - | - | 0.45 | °C/W |
| | R _{th(j-c)} | FWD | - | - | 0.73 | °C/W |
| Contact Thermal resistance | R _{th(c-f)} *5 | With thermal compound | - | 0.05 | - | °C/W |

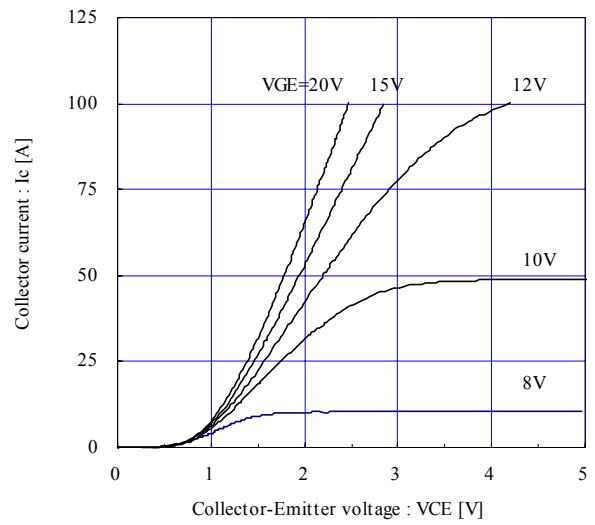
*5 : This is the value which is defined mounting on the additional cooling fin with thermal compound.

Characteristics (Representative)

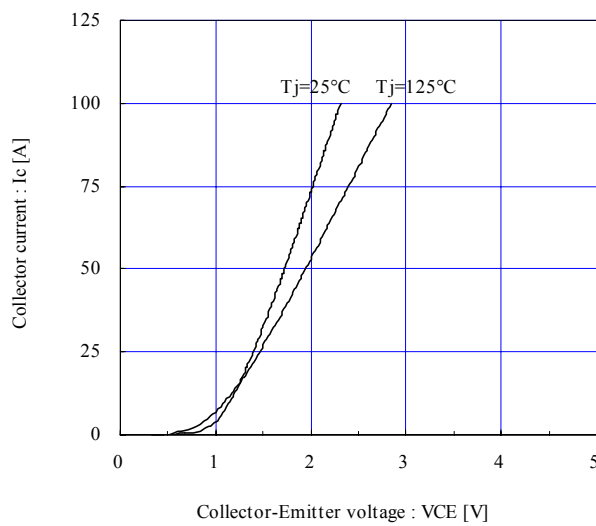
Collector current vs. Collector-Emitter voltage (typ.)
Tj= 25°C / chip



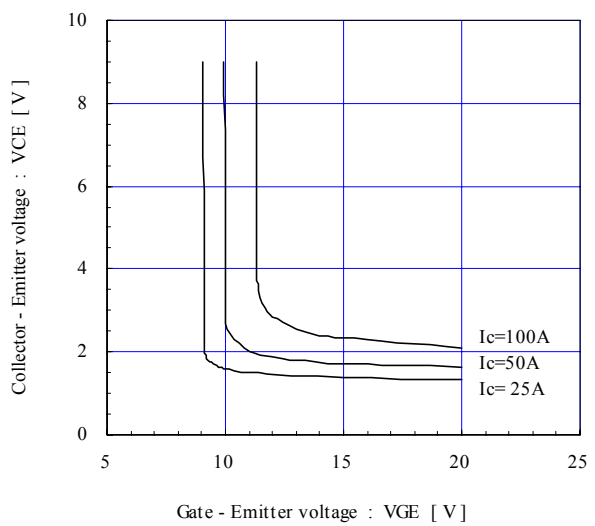
Collector current vs. Collector-Emitter voltage (typ.)
Tj= 125°C / chip



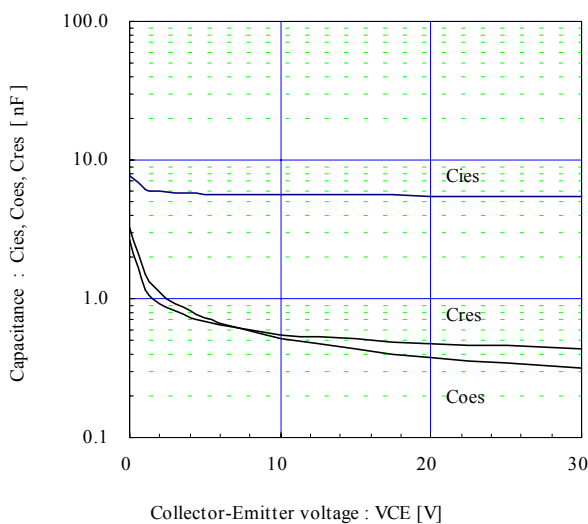
Collector current vs. Collector-Emitter voltage (typ.)
VGE=15V / chip



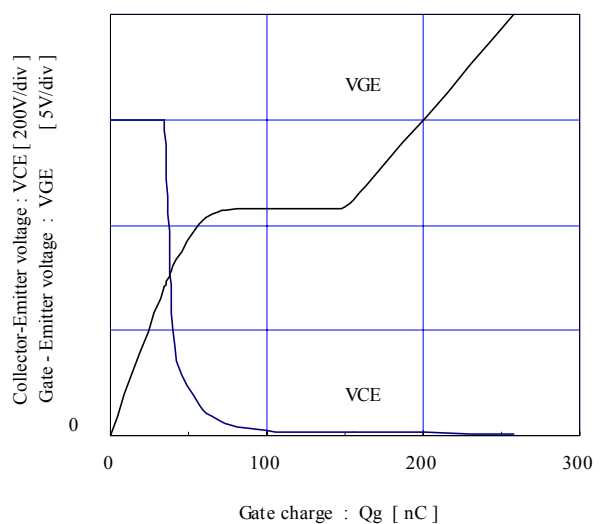
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)
Tj=25°C / chip



Capacitance vs. Collector-Emitter voltage (typ.)
VGE=0V, f= 1MHz, Tj= 25°C

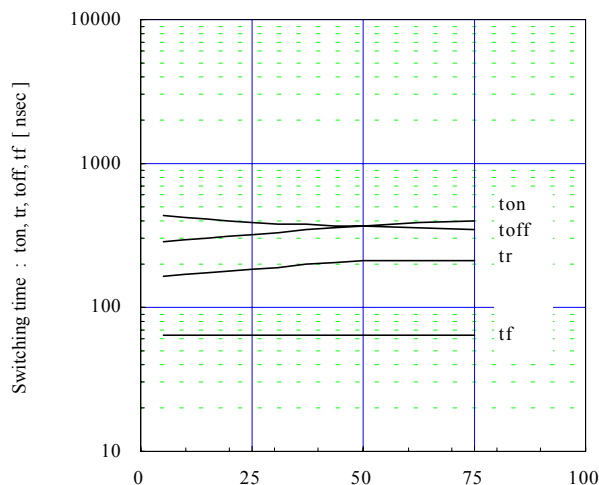


Dynamic Gate charge (typ.)
Vce=600V, Ic=50A, Tj= 25°C



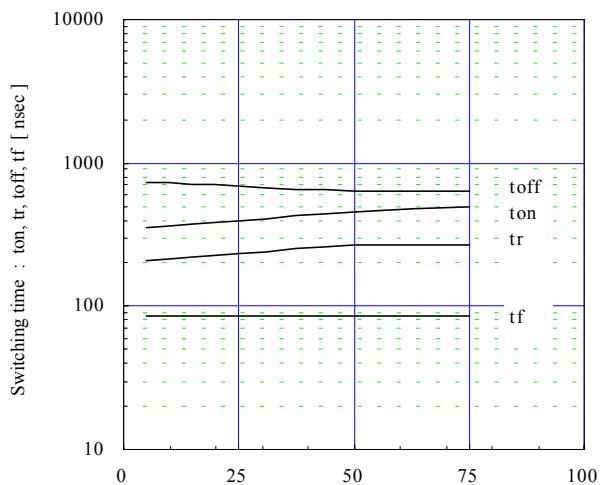
Switching time vs. Collector current (typ.)

$V_{cc}=600V, V_{GE}=\pm 15V, R_g=22\Omega, T_j=25^\circ C$



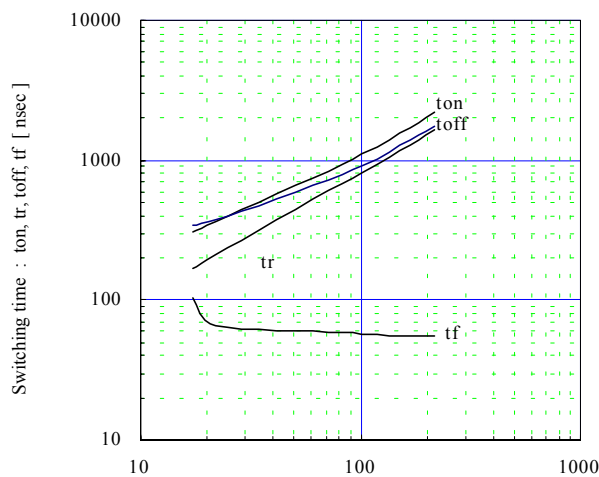
Switching time vs. Collector current (typ.)

$V_{cc}=600V, V_{GE}=\pm 15V, R_g=22\Omega, T_j=125^\circ C$



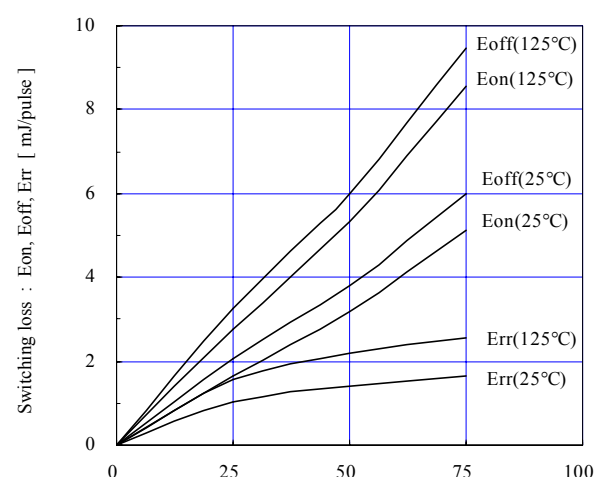
Switching time vs. Gate resistance (typ.)

$V_{cc}=600V, I_c=50A, V_{GE}=\pm 15V, T_j=25^\circ C$



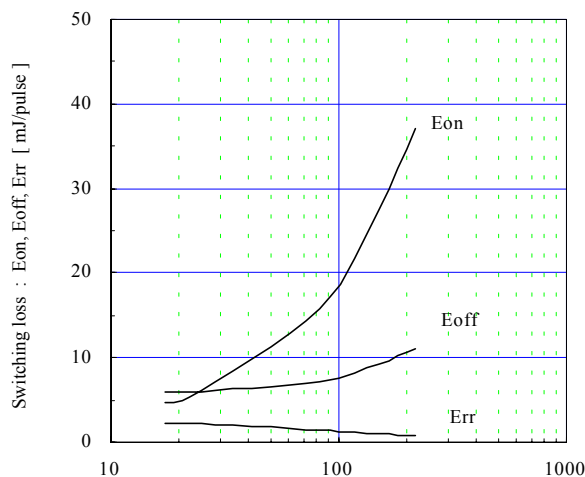
Switching loss vs. Collector current (typ.)

$V_{cc}=600V, V_{GE}=\pm 15V, R_g=22\Omega$



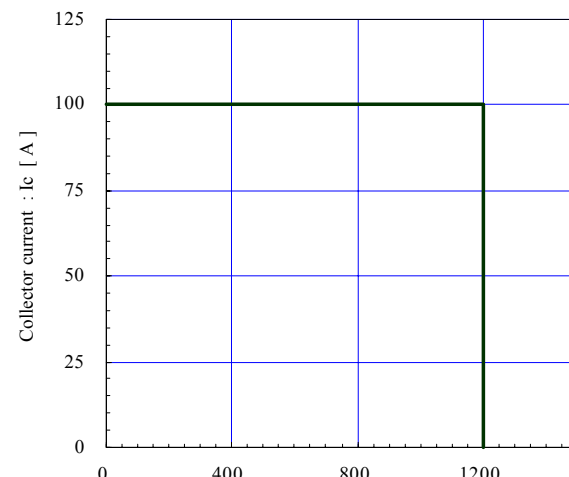
Switching loss vs. Gate resistance (typ.)

$V_{cc}=600V, I_c=50A, V_{GE}=\pm 15V, T_j=125^\circ C$

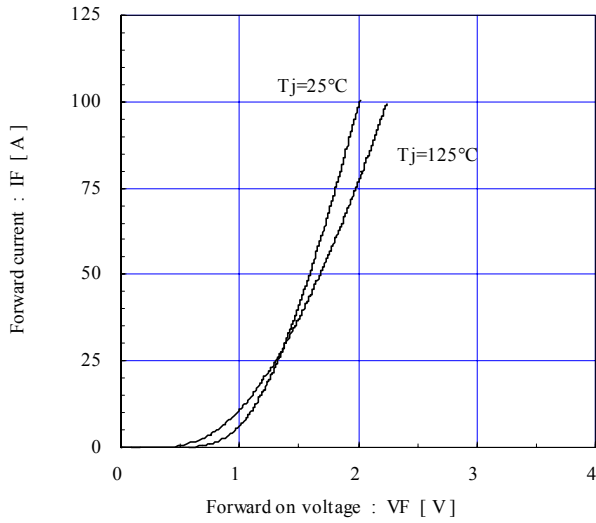


Reverse bias safe operating area (max.)

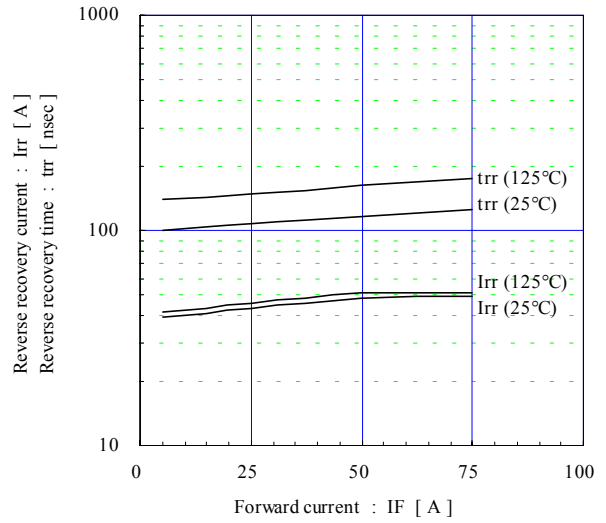
$+V_{GE}=15V, -V_{GE} \le 15V, R_g \ge 22\Omega, T_j \le 125^\circ C$



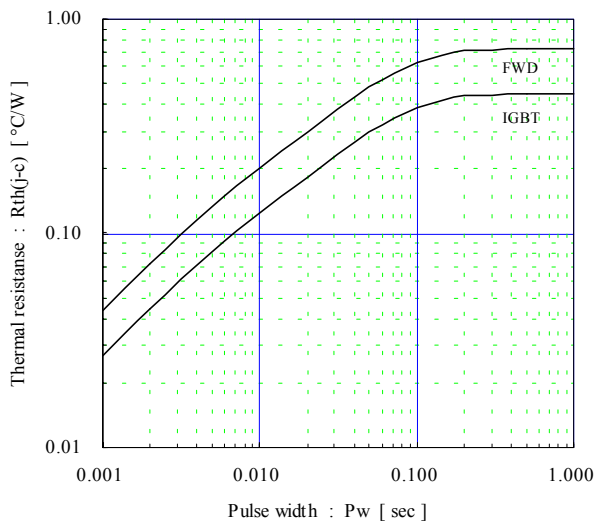
Forward current vs. Forward on voltage (typ.)
chip



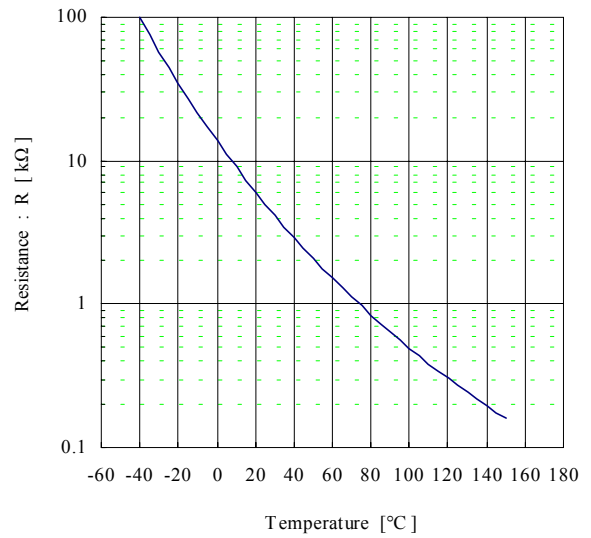
Reverse recovery characteristics (typ.)
 $V_{cc}=600\text{V}$, $V_{GE}=\pm 15\text{V}$, $R_g=22\Omega$



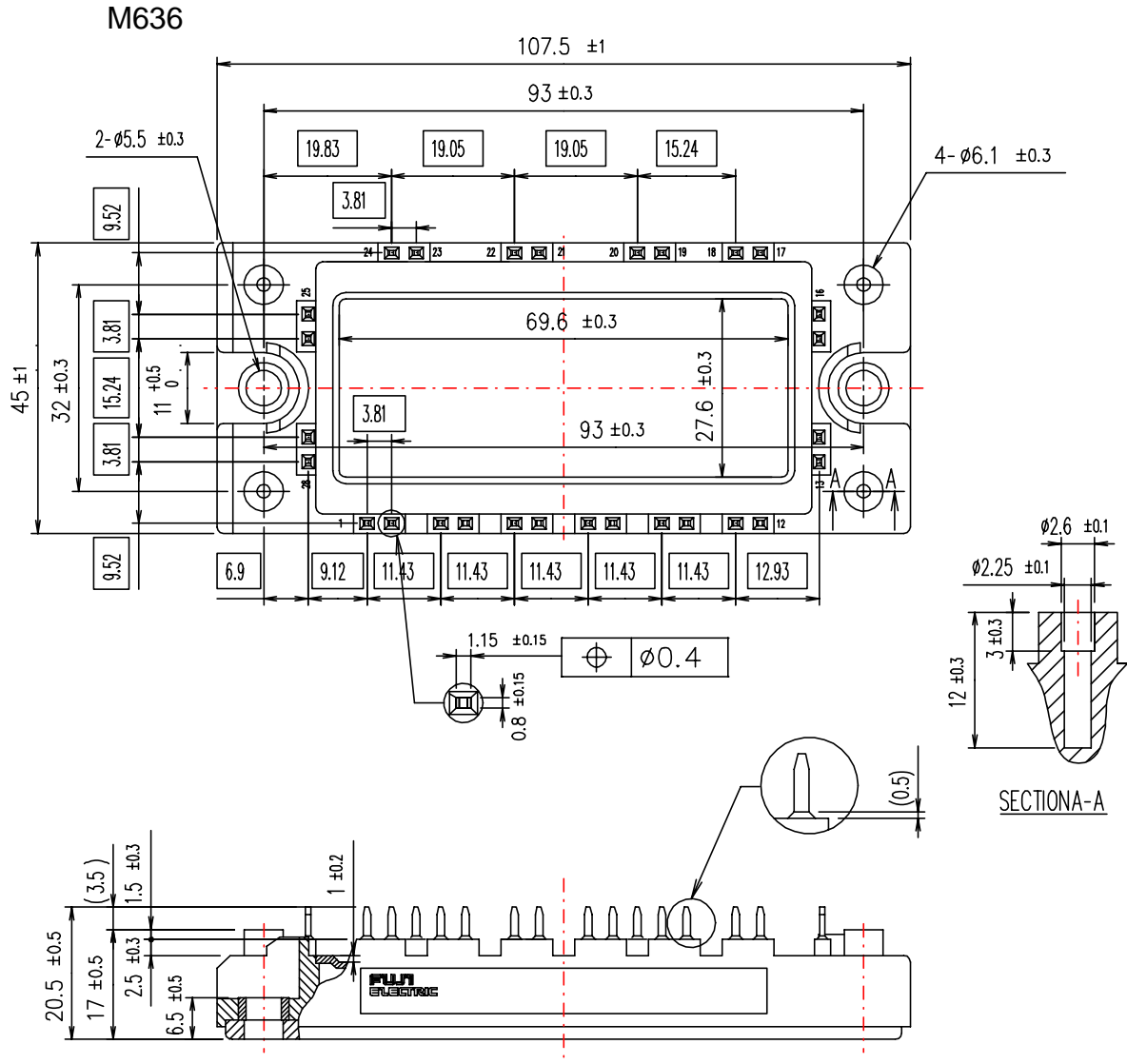
Transient thermal resistance (max.)



Temperature characteristic (typ.)

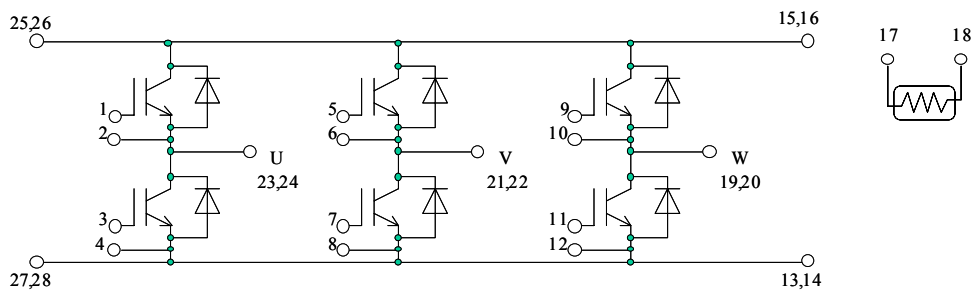


■ Outline Drawings, mm



□ shows theoretical dimension.
 () shows reference dimension.

■ Equivalent Circuit Schematic



This datasheet has been downloaded from:

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